

SINGLE CRYSTAL SAPPHIRE



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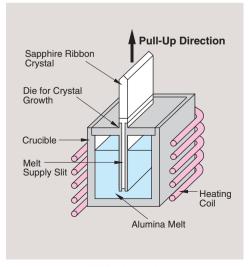
Single Crystal Sapphire is playing an ever-increasingly important role as a material for, high reliablility Electronics today due to its excellent mechanical characteristics, chemical stability and light transmission.

Kyocera mass-produces Single Crystal Sapphire in a vertically integrated manner. From "pulling up" the raw material with EFG (Edge-Defined Film-Fed Growth) methods to machining, Kyocera produces and supplies various products with large diameters or specific shape requirements.

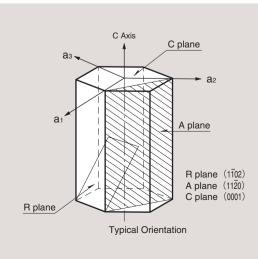
FEATURES OF EFG METHOD

- Large Size Material
 - Sizing-up of materials allows for a broader range of applications and uses.
- Production of Single Crystal Sapphire in Any Desired Sectional Shape
 Since any desired sectional shape can be obtained in the form of ribbons, tubes, rods, and others, cutting processes can be eliminated, allowing for a reduction in cost.
- Control of Crystal Orientation

Any axis and plane can be produced by instituting proper control during crystal growth.







Unit Cell of Sapphire

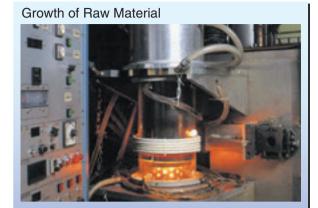
FEATURES OF SINGLE CRYSTAL SAPPHIRE

- High Strength, High Rigidity, High Anti-Abrasion, High Anti-Heat, High Anti-Corrosion Characteristics, and High Anti-Plasma Characteristics.
- Because of these characteristics, Single Crystal Sapphire is widely used for precision mechanical parts.
- Stable Dielectric Constant, Very Low Dielectric Loss, Good Electrical Insulation Single Crystal Sapphire is used as a material for substrates in super-high frequency regions. It is also used as an insulation material and microwave window. Single Crystal Sapphire has become indispensable in the Electronics Industries.
- Excellent Light Transmission Single Crystal Sapphire is used for various kinds of vacuum equipment, windows in reaction furnace, scanner windows and caps for optical communication due to its excellent mechanical characteristics and heat resistance.
- Good Thermal Conductivity and High Heat Resistance Excellent thermal conductivity at low temperatures allows Single Crystal Sapphire as a transparent material to be used in many diverse fields requiring thermal conduction and heat radiation.

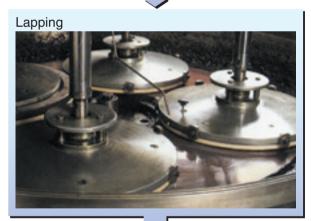


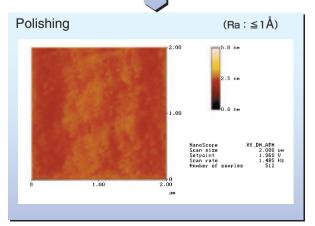
SAPPHIRE MANUFACTURING PROCESS

Sapphire Manufacturing Process



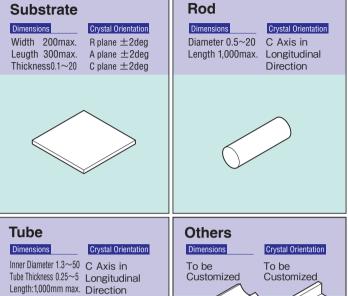






Shape and Specifications

(unit: mm)







*Shapes other than above are available.

As-Grown Materials





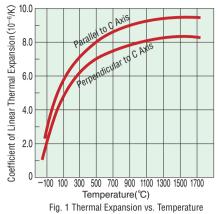
CHARACTERISTICS OF SINGLE CRYSTAL SAPPHIRE

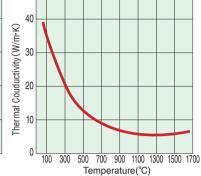
Characteristics of Kyocera's Single Crystal Sapphire

Characteristics of Kyocera's Single Crystal Sappnire							
Mechanical Characteristics	Crystallographic	Hexagonal System a=4.763Å					
	Structure	c=13.003Å					
		Rhombohedral Single crystal					
	Reference Density	3.97×10 ³ kg/m ³					
	Vickers Hardness	22.5GPa (HV1(Load=9.807N))					
	Flexural Strength	690MPa					
	Tanaila Ctranath	2250MPa					
	Tensile Strength	(Diameter0.25mm Filament 25°C)					
lech	Compressive Strength	2,940MPa					
2	Young's Modulus	470GPa					
	Poisson's Ratio	0.18~0.29					
Characteristics	Melting Point	2,053℃					
	Coefficient of Linear Thermal Expansion	40~400°C C parallel to Caxis 7.7×10°°/°C					
acte		40~400°C C perpendicular 7.0×10-6/°C					
har	Thermal Conductivity	20°C 42W/(m·k)					
a C	Specific Heat Capacity	0.75J/(g · K)					
Thermal	Emittance	<0.02					
Ļ		$(\lambda = 2.6 \sim 3.7 \mu\text{m880}^{\circ}\text{C})$					
S	Dielectric strength	48×10 ⁶ V/m					
stic	Volume Resistance	20°C $>10^{14}\Omega \cdot \text{cm}$					
idri		500°C 10¹¹Ω · cm					
Electrical Charac	Dielectric Constant	C parallel to Caxis 11.5 (1MHz)					
		C perpendicular to Caxis 9.3 (1MHz)					
	Dielectric Loss Angle	<1 (×10 ⁻⁴) (1MHz)					
	Loss Factor	- (×10 ⁻⁴)					
	Dielectric Loss Tangent	10 ⁻⁴ max.					
Characteristics	1.1. (5.0.)	No=1.768					
	Index of Reflection	Ne=1.760 @589nm					
Optical	Optical Transmission	Refer to Fig.5					

[%]These figures are representative.

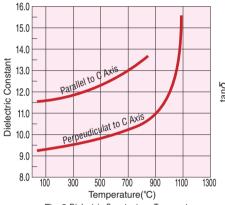
Standard Dimensional Tolerance





50

Fig. 2 Thermal Conductivity vs. Temperature



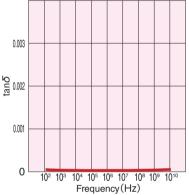


Fig. 3 Dielectric Constant vs. Temperature

Fig. 4 Dielectric Loss vs. Frequency

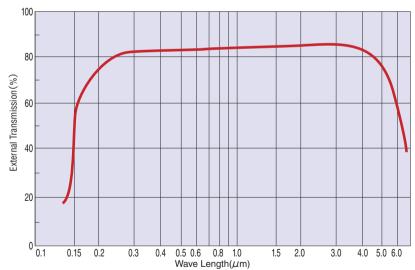


Fig. 5 Transmission vs. Wave Length

NOTE: •Transmittance range varies depending on thickness of Sapphire Products.

•Interfacial Reflection included

Thickness 1mm.

(Unit: mm)

Nominal Dimension : a	1>a	1≦a≦4	4 <a≦25< th=""><th>25<a≦102< th=""><th>102<a≦190< th=""><th>190<a< th=""></a<></th></a≦190<></th></a≦102<></th></a≦25<>	25 <a≦102< th=""><th>102<a≦190< th=""><th>190<a< th=""></a<></th></a≦190<></th></a≦102<>	102 <a≦190< th=""><th>190<a< th=""></a<></th></a≦190<>	190 <a< th=""></a<>	
Tolerance (±)	0.05	0.1	0.2	0.25	0.5	1	

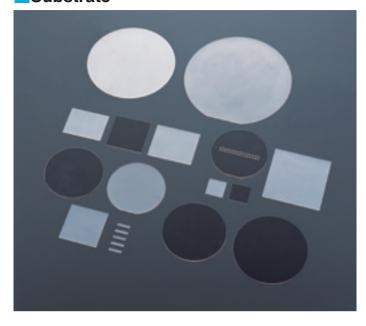
lacktriangle Machining accuracy: Tube 1.A.10.A.and standard tube thickness tolerance… ± 0.25 . Hole diameter and standard pitch tolerance… ± 0.1

^{*}Each Crystal Orientation has different characteristics.



SAPPHIRE PRODUCTS

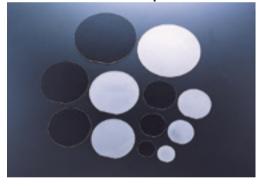
Substrate



Application

- (1) High Brightness LED
- (2) HB-LED Semiconductor, Piezoelectric Semiconductor, Superconductor, Thin Film Substrate.
- (3)MR Sensor, Precision Resistor
- (4)Optical Devices
- (5)Thin Film HIC
- Single Crystal Sapphire is widely used substrate material for blue, green, ultraviolet and white LEDs. It has excellent features as a base substrate for GaN deposition and great mass-productivity. In addition, it can meet future larger-size demand.
- Single Crystal Sapphire is used as a base substrate in thin film deposition because of its lattice alignment match with a variety of semiconductor materials combined with excellent thermal and chemical stability.

■2"-8" substrate for Optical Devices

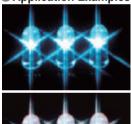


Standard Dimension and Tolerance

	Size	O.F. Length	
8″	φ 200±0.25×0.725±0.05	55~60	
6″	φ 150±0.25×0.625±0.05	45~50	
5″	ϕ 125 \pm 0.25 \times 0.625 \pm 0.05	40~45	
4″	ϕ 100 \pm 0.25 \times 0.53 \pm 0.05	30~35	
3″	ϕ 76.2 \pm 0.25 \times 0.43 \pm 0.05	19~25	
2″	ϕ 50.8 \pm 0.25 \times 0.33 \pm 0.05	13~19	

- *Specifications other than above are available.
- *Available sizes are dependent on a crystal orientation. Sizes and tolerances other than the above table are also available under customer requirements. Please contact or send your requirements to Kyocera.

Application Examples





Semiconductor Process Equipment Parts



Application

- (1)Carrier Plate
- (2)Microwave Entrance Tube
- (3)Dummy Water
- (4)Handling Arm
- (5) Vacuum Chuck
- (6)Window
- It is used as various Semiconductor Process Equipment due to its high anti-plasma and high anti-heat characteristics.













Optical Products for LCD Projectors



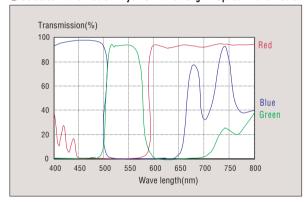
JP Patent No. 3091183, No.3443549 U.S. Patent No. 6577375, No.6642989

Application

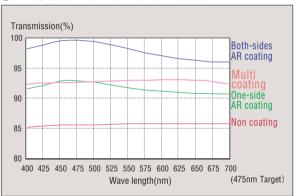
- (1) Sapphire Plate
 - · Polarizing Film Attached
 - Holder Assembled
 - · Dichroic Filter
- (2) LCD Projector

 Dust Control Plate
- Sapphire material realizes high brightness and high picture quality for LCD projectors due to its high thermal conductivity and optical properties.
- Coating such as Dichroic Filter, to prevent reflection features is available.
- Standard sizes to fit in various LCD panels are available.

Selected Transmission Layer for Wave Length Optical Transmission



AR Coat External Transmission



*Characteristic values are subjected to change due to each specs or conditions.

Optical Products



Application

(1)POS Scanner Window (SOG)
(2)Window
(3)Cap for Optical Communication
(4)Infrared Measuring Device Window
(5)Coin Sensor

(6)Lamp External Tube High Pressure Sodium, Xenon, Ultra Pressure mercury Metallic Halide (7)Light Receiving Window Accelerating

Tube

Application

(1)Fiber Bar Guide
(2)Insulating Plate and Rod
(3)Single Crystal Material Sheel Holder
(4)Biomaterial (BIOCERAM®)
(5)Watch Window
(6)MMR Protection Tube

(7)Thermocouple Protection Tube (8)HDC Resonator Rod

Others



KYOCERA Corporation Corporate Fine Ceramics Group

https://global.kyocera.com/prdct/fc/

Kyocera Fine Ceramics



